

Investigation of Charge Multiplication in Silicon Strip Detectors

Thursday, 31 May 2012 17:00 (20 minutes)

Samples of n-in-p sensors provided by the RD50 collaboration have been irradiated with protons to fluences of $1e15$, $5e15$ and $1e16$ neq/cm². An overview of the sensor properties before and after irradiation will be presented. After irradiation an annealing study of signal, signal to noise and leakage current has been performed with the ALiBaVa setup at different annealing steps up to 500 days at room temperature.

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